



Lead-free Green

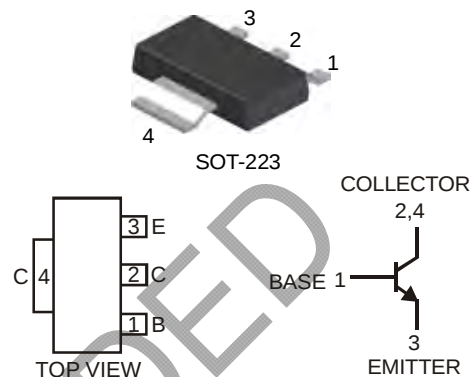
LOW VCE(SAT) NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Resistance $R_{CE(SAT)} = 57.5m\Omega$ at 4A
- High DC Current Gain $h_{FE} > 400$ at $I_C = 3A$
- Complementary PNP Type Available (DPLS315E)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish — Matte Tin annealed over Copper Leadframe
(Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	12	V
Collector-Emitter Voltage	V_{CEO}	12	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	4	A
Peak Pulse Current	I_{CM}	10	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @ $T_A = 25^\circ C$ (Note 3)	P_D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @ $T_A = 25^\circ C$	$R_{\theta JA}$	125	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
1. No purposefully added lead.
 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 3. Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Off Characteristics						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	12	—	—	V	I _C = 100μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	12	—	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	—	—	V	I _E = 100μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	—	100	nA	V _{CB} = 10V, I _E = 0
Emitter Cutoff Current	I _{EBO}	—	—	100	nA	V _{EB} = 4V, I _C = 0
On Characteristics (Note 4)						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.02	0.04	V	I _C = 0.1A, I _B = 1mA
		—	0.03	0.06		I _C = 0.1A, I _B = 0.5mA
		—	0.06	0.18		I _C = 1A, I _B = 50mA
		—	0.20	0.35		I _C = 3A, I _B = 20mA
		—	0.23	0.40		I _C = 4A, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	—	1.1	V	I _C = 3A, I _B = 20mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	—	—	1.0	V	V _{CE} = 2V, I _C = 3A
DC Current Gain	h _{FE}	500	—	—	—	V _{CE} = 2V, I _C = 0.1A
		400	—	—		V _{CE} = 2V, I _C = 3A
		100	—	—		V _{CE} = 2V, I _C = 10A
AC Characteristics						
Transition Frequency	f _T	150	—	—	MHz	V _{CE} = 5V, I _C = 50mA, f = 50MHz
Input Capacitance	C _{ibo}	—	240	—	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	C _{obo}	—	35	—	pF	V _{CB} = 10V, f = 1MHz
Switching Times	t _{on}	—	40	—	ns	V _{CC} = 10V, I _C = 500mA
	t _{off}	—	500	—	ns	I _{B1} = -I _{B2} = 50mA

Notes: 4. Pulse Test: Pulse width ≤300μs. Duty cycle ≤2.0%.

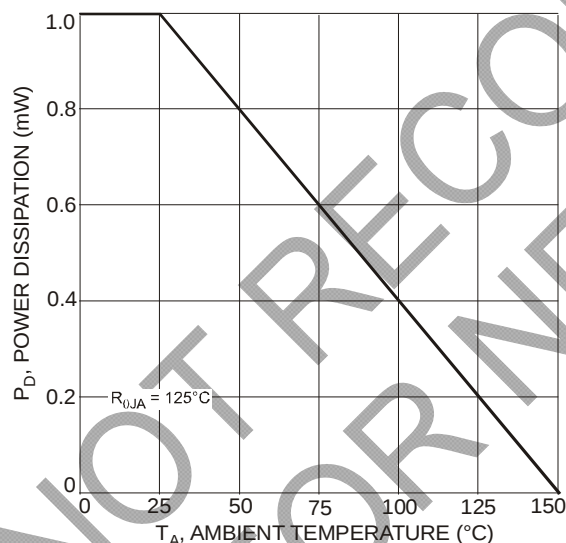


Fig. 1 Max Power Dissipation vs. Ambient Temperature

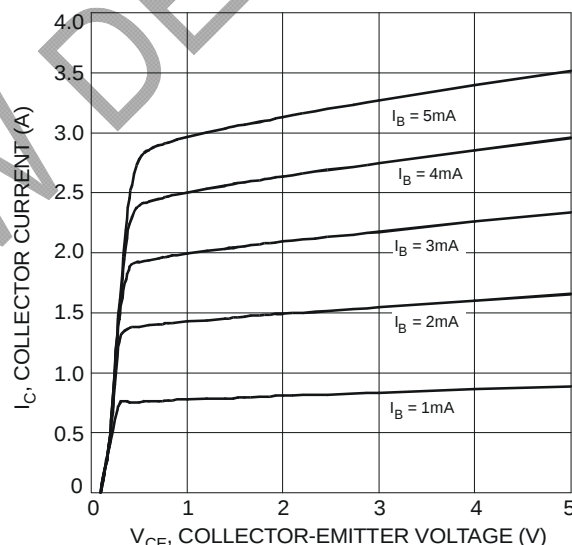


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

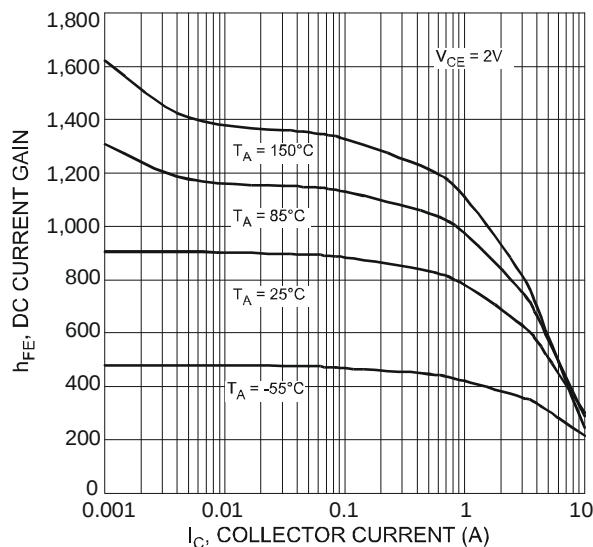


Fig. 3 Typical DC Current Gain vs. Collector Current

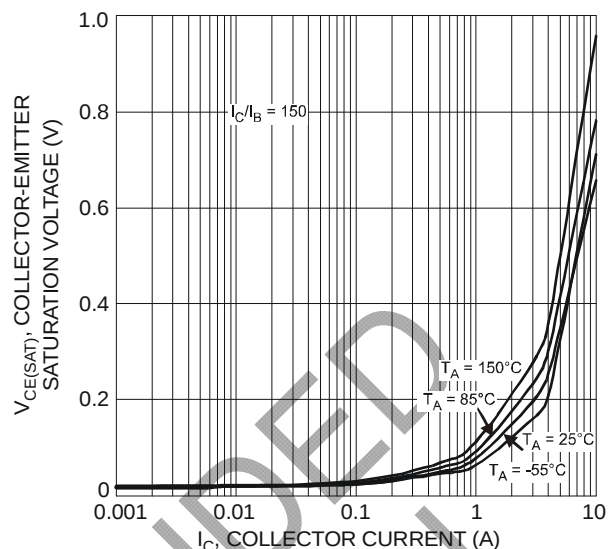


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

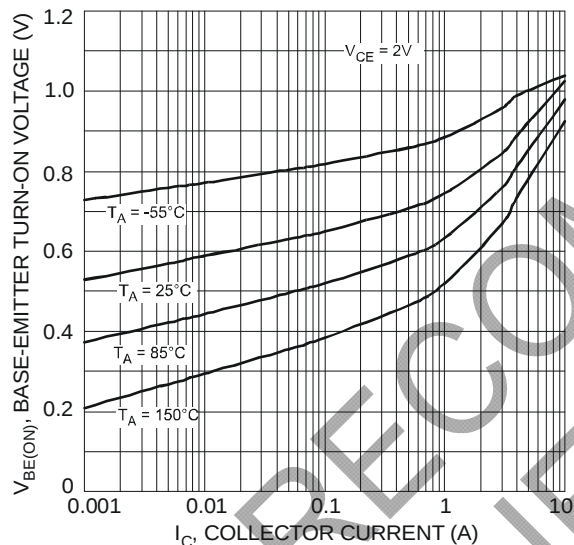


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

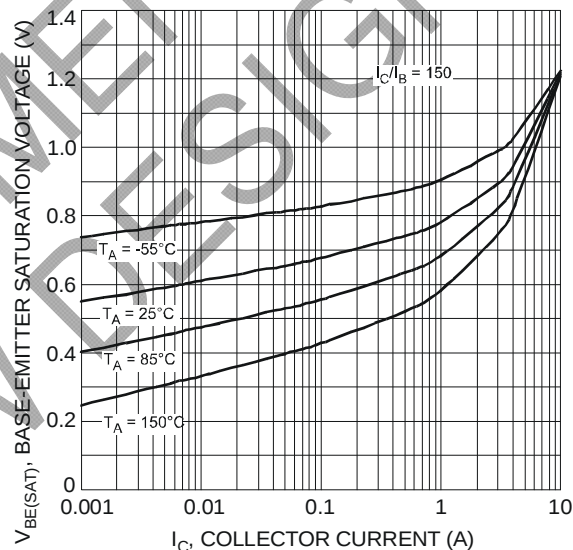


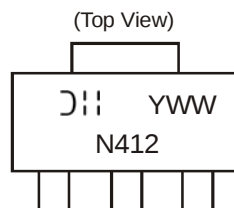
Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DNLS412E-13	SOT-223	2500/Tape & Reel

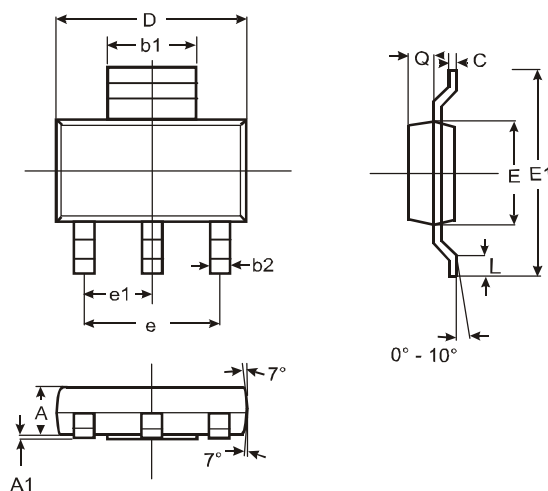
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/ap2007.pdf>.

Marking Information



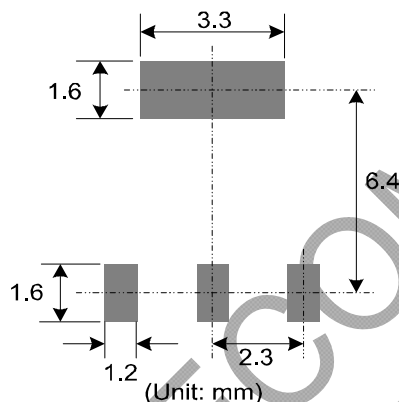
N412 = Product Type Marking Code
YWW = Date Code Marking
Y = Last digit of year ex: 7 = 2007
WW = Week code 01 - 52

Package Outline Dimensions



SOT-223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b1	2.90	3.10	3.00
b2	0.60	0.80	0.70
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	—	—	4.60
e1	—	—	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout:



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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9